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2N7002BK

60 V, 350 mA N-channel Trench MOSFET Rev. 1 — 17 June 2010

Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	-	±20	V
I_D	drain current	T_{amb} = 25 °C; V_{GS} = 10 V	[1] -	-	350	mA
R _{DSon}	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 500 \text{mA}$	-	1	1.6	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, 350 mA N-channel Trench MOSFET

017aaa000

2. Pinning information

Table 2. Pinning

Table 2.	Filling			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source	3	D
3	D	drain	1 2	G S S S S S S S S S S S S S S S S S S S

3. Ordering information

Table 3. Ordering information

Type number	Package	Package			
	Name	Description	Version		
2N7002BK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
2N7002BK	LN*

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I _D	drain current	$V_{GS} = 10 \text{ V}$	[1]		
		T _{amb} = 25 °C	-	350	mA
		T _{amb} = 100 °C	-	245	mA
I _{DM}	peak drain current	$T_{amb} = 25 ^{\circ}C;$ single pulse; $t_p \le 10 \mu s$	-	1.2	Α

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

60 V, 350 mA N-channel Trench MOSFET

Table 5. Limiting values ...continued In accordance with the Absolute Maximum Rating System (IEC 60134).

		• • •	•		
Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} = 25 ^{\circ}C$	[2] -	370	mW
			<u>[1]</u> -	440	mW
		T _{sp} = 25 °C	-	1.2	W
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C
Source-d	rain diode				
I _S	source current	T _{amb} = 25 °C	<u>[1]</u> -	350	mA
ESD max	imum rating				
V _{ESD}	electrostatic discharge voltage	human body model	[3] -	2000	V

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

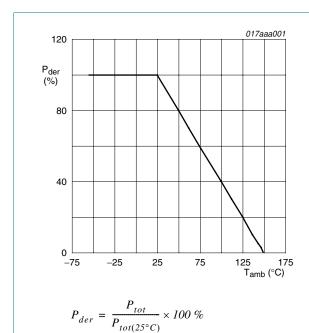
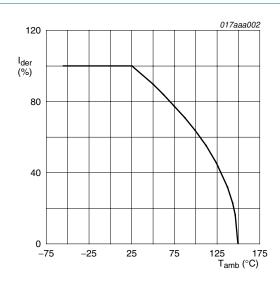


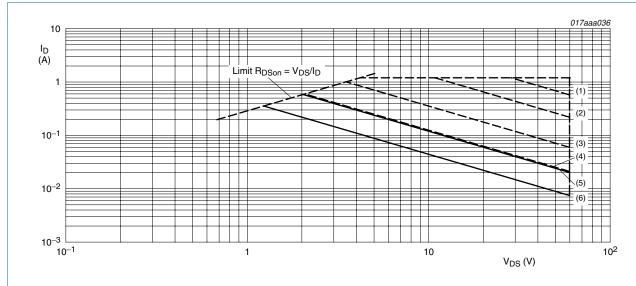
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100~\%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

60 V, 350 mA N-channel Trench MOSFET



 I_{DM} = single pulse

- (1) $t_p = 100 \ \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) $t_D = 100 \text{ ms}$
- (5) DC; $T_{sp} = 25 \, ^{\circ}C$
- (6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

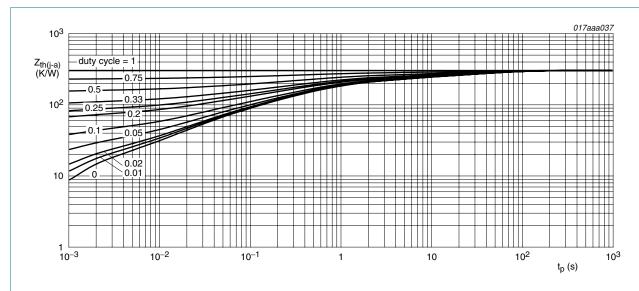
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	<u>[1]</u> -	295	340	K/W
	junction to ambient		[2] _	250	285	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	105	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

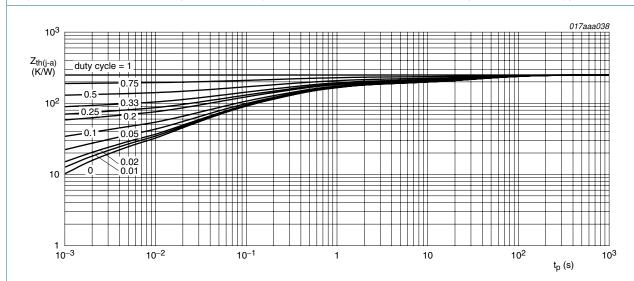
^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

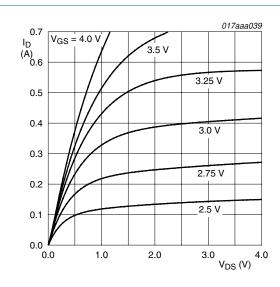
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D=10~\mu\text{A};V_{GS}=0~V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μΑ
		T _j = 150 °C	-	-	10	μА
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	10	μА
R _{DSon}	drain-source on-state resistance		<u>[1]</u>			
		$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$	-	1.3	2	Ω
		$V_{GS} = 10 \text{ V}; I_D = 500 \text{ mA}$	-	1	1.6	Ω
9fs	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	<u>[1]</u> _	550	-	mS
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 300 \text{ mA};$	-	0.5	0.6	nC
Q_{GS}	gate-source charge	[−] V _{DS} = 30 V; − V _{GS} = 4.5 V	-	0.2	-	nC
Q_{GD}	gate-drain charge	VGS = 4.5 V	-	0.1	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \ V; \ V_{DS} = 10 \ V;$	-	33	50	pF
Coss	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DD} = 50 \text{ V};$	-	5	10	ns
t _r	rise time	$R_L = 250 \Omega;$ - $V_{GS} = 10 V;$	-	6	-	ns
$t_{d(off)}$	turn-off delay time	$R_{G} = 6 \Omega$	-	12	24	ns
t _f	fall time		-	7	-	ns
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	V

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

10-3

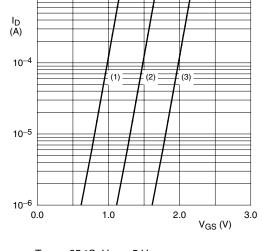
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T_{amb} = 25 °C

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



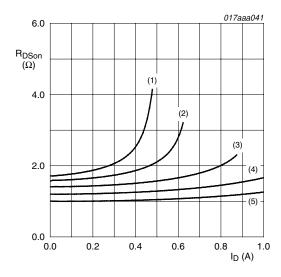
 $T_{amb} = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



T_{amb} = 25 °C

(1) $V_{GS} = 3.25 \text{ V}$

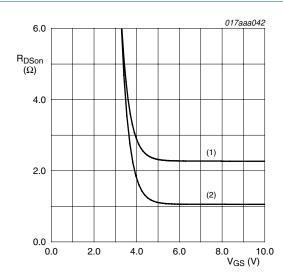
(2) $V_{GS} = 3.5 \text{ V}$

(3) $V_{GS} = 4 V$

(4) $V_{GS} = 5 V$

(5) $V_{GS} = 10 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



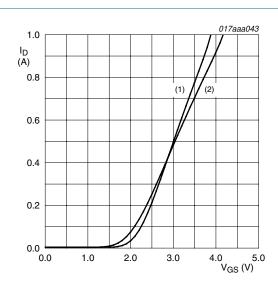
 $I_D = 500 \text{ mA}$

(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

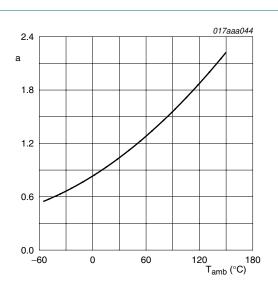
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$$V_{DS} > I_D \times R_{DSon}$$

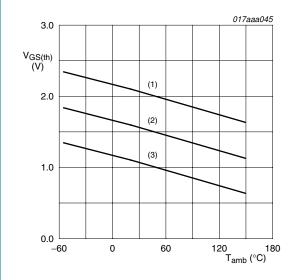
- (1) $T_{amb} = 25 \, ^{\circ}C$
- (2) $T_{amb} = 150 \, ^{\circ}C$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

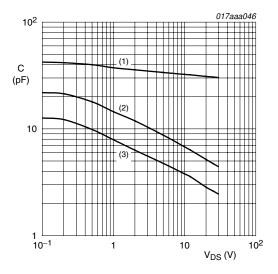
Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of ambient temperature

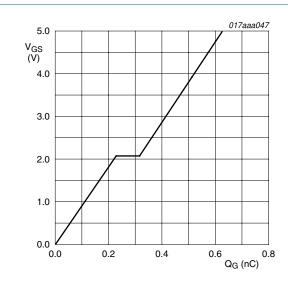


$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 I_D = 300 mA; V_{DD} = 6 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

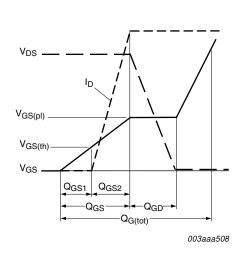
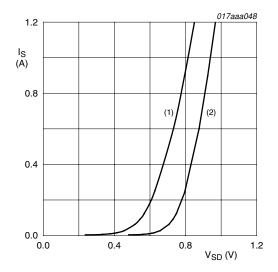


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

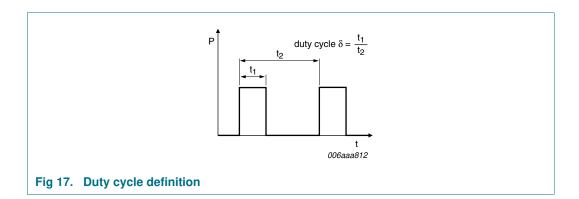
(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



60 V, 350 mA N-channel Trench MOSFET

9. Package outline

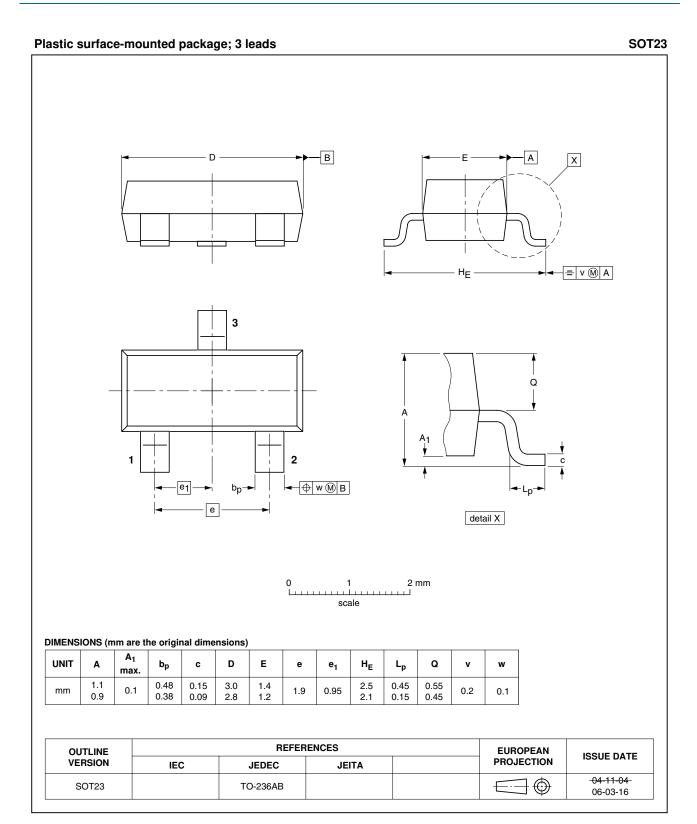


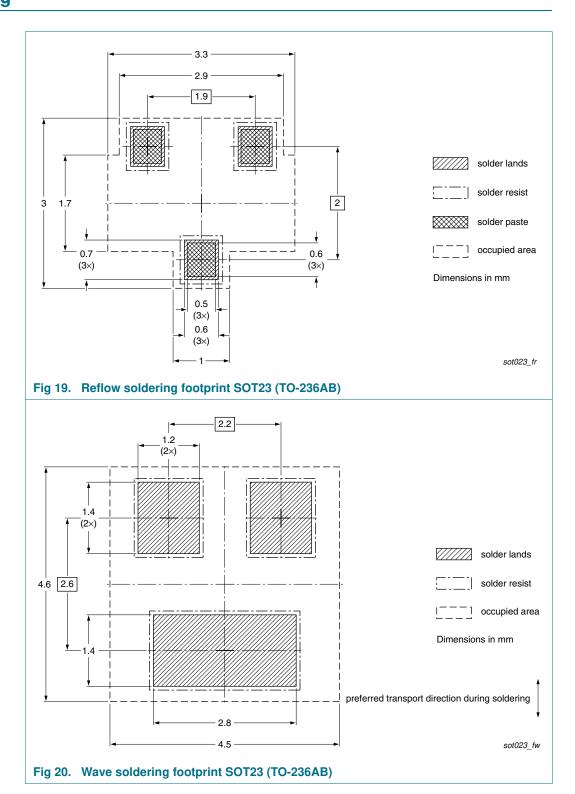
Fig 18. Package outline SOT23 (TO-236AB)

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60 V, 350 mA N-channel Trench MOSFET

10. Soldering



60 V, 350 mA N-channel Trench MOSFET

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002BK v.1	20100617	Product data sheet	-	-

60 V, 350 mA N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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2N7002BK **NXP Semiconductors**

60 V, 350 mA N-channel Trench MOSFET

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60 V, 350 mA N-channel Trench MOSFET

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